

# Adam J Barcz

## List of Publications by Year in descending order

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81  
papers

967  
citations

516710

16  
h-index

477307

29  
g-index

81  
all docs

81  
docs citations

81  
times ranked

1229  
citing authors

#	ARTICLE	IF	CITATIONS
1	SIMS accurate determination of matrix composition of topological crystalline insulator material $Pb_{1-x}Sn_xSe$ . <i>Surface and Interface Analysis</i> , 2020, 52, 71-75.	1.8	3
2	Investigation of diffusion mechanism of beryllium in GaN. <i>Physica B: Condensed Matter</i> , 2020, 594, 412316.	2.7	8
3	Ion-Irradiated Damage in Semiconductors Visualized by Means of Low-kV Scanning Electron Microscopy. <i>Microscopy and Microanalysis</i> , 2019, 25, 486-487.	0.4	1
4	Damage-induced voltage alteration (DIVA) contrast in SEM images of ion-irradiated semiconductors. <i>Ultramicroscopy</i> , 2019, 204, 6-9.	1.9	3
5	Diffusion of Mn in gallium nitride: Experiment and modelling. <i>Journal of Alloys and Compounds</i> , 2019, 771, 215-220.	5.5	13
6	Analysis of defect structure in GaN epilayers doped with implanted $Si^+$ by RBS/c method. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2019, 450, 248-251.	1.4	5
7	Electrical isolation of GaAs and AlGaAs/GaAs Quantum Cascade Lasers by deep hydrogen implantation. <i>Materials Science in Semiconductor Processing</i> , 2018, 74, 88-97.	4.0	2
8	Ultrahigh sensitivity SIMS analysis of oxygen in silicon. <i>Surface and Interface Analysis</i> , 2018, 50, 729-733.	1.8	10
9	Resonant Photoemission Spectroscopy Study on the Contribution of the Yb 4f States to the Electronic Structure of ZnO. <i>Acta Physica Polonica A</i> , 2018, 133, 907-909.	0.5	9
10	Communication – Direct Imaging of Irradiation Damage in Semiconductors by Low-Energy SEM. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P415-P417.	1.8	5
11	Proton implantation for the isolation of AlGaAs/GaAs quantum cascade lasers. <i>Semiconductor Science and Technology</i> , 2016, 31, 075010.	2.0	7
12	Observation of surface states on heavily indium-doped SnTe(111), a superconducting topological crystalline insulator. <i>Physical Review B</i> , 2016, 93, .	3.2	27
13	Incorporation of oxygen in SiC implanted with hydrogen. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2015, 365, 146-149.	1.4	4
14	Ion implantation for isolation of AlGaIn/GaN HEMTs using C or Al. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015, 212, 1162-1169.	1.8	34
15	Response of ZnO/GaN Heterostructure to Ion Irradiation. <i>Acta Physica Polonica A</i> , 2015, 128, 832-835.	0.5	0
16	Diffusion and impurity segregation in hydrogen-implanted silicon carbide. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	26
17	XPS study of arsenic doped ZnO grown by Atomic Layer Deposition. <i>Journal of Alloys and Compounds</i> , 2014, 582, 594-597.	5.5	25
18	Analysis of Crystal Lattice Deformation by Ion Channeling. <i>Acta Physica Polonica A</i> , 2013, 123, 828-830.	0.5	10

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19	Performance of a nitrogen implanted large aperture THz emitter. Photonics Letters of Poland, 2012, 4, .	0.4	0
20	Silicon detectors for the sLHC. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 658, 11-16.	1.6	21
21	Oxygen diffusion into GaN from oxygen implanted GaN or Al <sub>2</sub> O <sub>3</sub> . Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1513-1515.	0.8	11
22	Hydrogen Gettering within Processed Oxygen-Implanted Silicon. Advanced Materials Research, 2011, 276, 35-40.	0.3	0
23	Structure of self-implanted silicon annealed under enhanced hydrostatic pressure. High Pressure Research, 2011, 31, 102-105.	1.2	0
24	Properties of Si:V Annealed under Enhanced Hydrostatic Pressure. Acta Physica Polonica A, 2011, 120, 196-199.	0.5	0
25	Silicon Dioxide as a Boundary for Oxygen Outdiffusion from CZ-Si. Defect and Diffusion Forum, 2010, 297-301, 688-693.	0.4	0
26	Study of the Local Environment of Mn Ions Implanted in GaSb. Acta Physica Polonica A, 2010, 117, 286-292.	0.5	4
27	Defect Structure of High-Temperature-Grown GaMnSb/GaSb. Acta Physica Polonica A, 2010, 117, 341-343.	0.5	8
28	Origin of Magnetic Circular Dichroism in GaMnAs: Giant Zeeman Splitting versus Spin Dependent Density of States. Physical Review Letters, 2009, 102, 247202.	7.8	27
29	Structural and magnetic properties of the molecular beam epitaxy grown MnSb layers on GaAs substrates. Journal of Applied Physics, 2009, 106, .	2.5	9
30	Response to "Comment on "Common origin of ferromagnetism and band edge Zeeman splitting in GaMnAs at low Mn concentrations" [Appl. Phys. Lett. 94, 156101 (2009)]. Applied Physics Letters, 2009, 94, 156102.	3.3	1
31	Effect of processing on microstructure of Si:Mn. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 99-102.	3.5	8
32	Buried spongy-like layers in silicon implanted with He+, annealed and treated in D+plasma. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1551-1556.	0.8	2
33	Deuterium accumulation within nano-structured layers in Si:He upon plasma treatment. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2789-2791.	0.8	0
34	Stress-mediated redistribution of Mn in annealed Si:Mn. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 361-364.	3.5	3
35	Common origin of ferromagnetism and band edge Zeeman splitting in GaMnAs at low Mn concentrations. Applied Physics Letters, 2007, 91, 171118.	3.3	24
36	Properties of Si:Cr Annealed under Enhanced Stress Conditions. Solid State Phenomena, 2007, 131-133, 375-380.	0.3	3

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37	Investigation of the Hydrogen Transport Processes in Crystalline Silicon of n-Type Conductivity. Solid State Phenomena, 2007, 131-133, 425-430.	0.3	2
38	New Chemical Method of Obtaining Thick Ga <sub>1-x</sub> Mn <sub>x</sub> N Layers: A Prospective Spintronic Material. Chemistry of Materials, 2007, 19, 3139-3143.	6.7	11
39	Growth and structural properties of thick GaN layers obtained by sublimation sandwich method. Journal of Crystal Growth, 2007, 303, 395-399.	1.5	9
40	Pressure mediated release of hydrogen from silicon co-implanted with H <sub>2</sub> <sup>+</sup> and He <sup>+</sup> . Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2011-2015.	0.8	0
41	Determination of Mn Acceptor Compensation in MBE-Grown GaMnAs via Magnetic Circular Dichroism (MCD). IEEE Transactions on Magnetics, 2007, 43, 3031-3033.	2.1	8
42	Diffusion of Mn in gallium arsenide. Journal of Alloys and Compounds, 2006, 423, 132-135.	5.5	6
43	Si diffusion in epitaxial GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1416-1419.	0.8	24
44	Pressure-induced transformations of nitrogen implanted into silicon. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 781-785.	1.8	1
45	Electrical activity of deep levels in the presence of InAs/GaAs quantum dots. Materials Science in Semiconductor Processing, 2006, 9, 36-40.	4.0	8
46	Effect of pressure annealing on structure of Si:Mn. Materials Science in Semiconductor Processing, 2006, 9, 270-274.	4.0	10
47	New Silicon-Based Materials for Spintronics Applications - Si:V and Si:Cr. ECS Transactions, 2006, 3, 481-489.	0.5	3
48	Properties of ZrN films as substrate masks in liquid phase epitaxial lateral overgrowth of compound semiconductors. Crystal Research and Technology, 2005, 40, 492-497.	1.3	6
49	ZnO-based p-n Junctions with p-type ZnO by ZnTe Oxidation. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	0
50	Evolution of defect structure of Ge-implanted Si crystal during nanosecond laser annealing. EPJ Applied Physics, 2004, 27, 149-153.	0.7	1
51	Effects of electron concentration on the optical absorption edge of InN. Applied Physics Letters, 2004, 84, 2805-2807.	3.3	221
52	Doping of low-temperature GaAs and GaMnAs with carbon. Applied Physics Letters, 2004, 85, 4678-4680.	3.3	9
53	Out- and in-diffusion of oxygen <sup>16</sup> O in silicon. Semiconductor Science and Technology, 2004, 19, 1311-1314.	2.0	11
54	Cr <sup>3+</sup> ions in hydrogenated and proton exchanged lithium niobate crystals. Physica Status Solidi A, 2004, 201, 298-303.	1.7	0

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55	High temperature arsenic doping of CdHgTe epitaxial layers. Crystal Research and Technology, 2004, 39, 11-22.	1.3	5
56	Peculiarities of thin film deposition by means of reactive impulse plasma assisted chemical vapor deposition (RIPACVD) method. Thin Solid Films, 2004, 459, 160-164.	1.8	18
57	Recrystallisation and dopant diffusion in amorphised germanium layers upon pulsed laser annealing. Journal of Alloys and Compounds, 2004, 362, 265-268.	5.5	5
58	High-quality p-n junction fabrication by ion implantation using the LPCVD amorphous silicon films. Vacuum, 2003, 70, 81-85.	3.5	0
59	Diffusion and activation of Si implanted into GaAs. Vacuum, 2003, 70, 97-101.	3.5	8
60	Extremely deep SIMS profiling: oxygen in FZ silicon. Applied Surface Science, 2003, 203-204, 396-399.	6.1	16
61	Porous-like silicon prepared from Si:H annealed at high argon pressure. Physica Status Solidi A, 2003, 197, 236-240.	1.7	3
62	Effect of External Stress at Annealing on Microstructure of Silicon Co-Implanted with Hydrogen and Helium. Solid State Phenomena, 2003, 95-96, 313-318.	0.3	7
63	Influence of growth conditions on the lattice constant and composition of (Ga,Mn)As. Applied Physics Letters, 2003, 82, 4678-4680.	3.3	27
64	The microstructure and electrical properties of hydrogenated Czochralski silicon treated at high temperature and pressure. Journal of Physics Condensed Matter, 2003, 15, 7445-7453.	1.8	1
65	Controlled arsenic diffusion in epitaxial Cd <sub>x</sub> Hg <sub>1-x</sub> Te layers in the evaporation-condensation-diffusion process. Thin Solid Films, 2002, 403-404, 144-147.	1.8	3
66	Study of Zn-related structural transformations at p-GaAs/Ni/Zn interfaces relative to the formation of an ohmic contact. Materials Science in Semiconductor Processing, 2001, 4, 289-291.	4.0	3
67	Structure of Oxygen - Implanted Silicon Single Crystals Treated at ~1400 K under High Argon Pressure. Crystal Research and Technology, 2001, 36, 933-941.	1.3	10
68	Carrier-induced ferromagnetic interactions in p-doped Zn(1-x)MnxTe epilayers. Journal of Crystal Growth, 2000, 214-215, 387-390.	1.5	56
69	Cation diffusion in MBE-grown CdTe layers. Thin Solid Films, 2000, 367, 220-222.	1.8	11
70	Second metastable DX center in CdF <sub>2</sub> :Ga crystals. Physical Review B, 2000, 61, 9295-9299.	3.2	2
71	Effect of External Stress Applied during Annealing on Hydrogen- and Oxygen-Implanted Silicon. Solid State Phenomena, 1999, 69-70, 345-350.	0.3	20
72	Iodine-impurity level in MBE-grown Cd <sub>1-x</sub> MnxTe. Physical Review B, 1999, 59, 12917-12923.	3.2	6

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73	High mobility 2D electron gas in iodine modulation doped CdTe/CdMgTe heterostructures. Journal of Crystal Growth, 1998, 184-185, 814-817.	1.5	72
74	Channels of Cd diffusion and stoichiometry in CdTe grown by molecular beam epitaxy. Applied Physics Letters, 1998, 72, 206-208.	3.3	16
75	Modification of Al-based metallization for improved surface morphology. Microelectronic Engineering, 1997, 37-38, 341-346.	2.4	0
76	Manganese diffusion in MBE-grown Cd(Mn)Te structures. Journal of Crystal Growth, 1996, 159, 980-984.	1.5	21
77	X-ray electrono-optical and SIMS characterization of Si crystals implanted with Bi ions before and after rapid thermal annealing. Crystal Research and Technology, 1995, 30, 129-133.	1.3	3
78	Kinetic model of Au-GaAs interfacial reaction. Journal of Applied Physics, 1993, 74, 3172-3176.	2.5	7
79	Pulsed laser annealing of nitrogen-implanted GaP. Materials Letters, 1985, 3, 141-144.	2.6	1
80	Accumulation of Hydrogen within Implantation-Damaged Areas in Processed Si:N and Si:O. Solid State Phenomena, 0, 156-158, 319-324.	0.3	3
81	Solid Phase Epitaxial Re-Growth of Amorphous Layer in Si:Si Annealed under Enhanced Hydrostatic Pressure. Solid State Phenomena, 0, 178-179, 416-420.	0.3	0